(12) 按照专利合作条约所公布的国际申请

(54) Title: DATA WRITE-IN METHOD FOR FLASH MEMORY
(54) 发明名称: 闪存介质数据写入方法
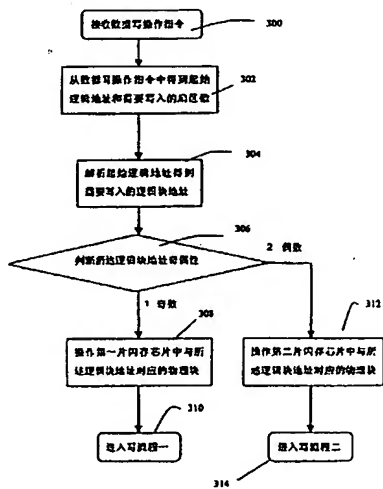
300	RECEIVE THE DATA WRITE IN OPERATING INSTRUCTION
302	OBTAIN THE START LOGICAL ADDRESS AND THE NUMBER OF THE SECTOR THAT SHOULD BE WROTE-IN ACCORDING TO THE DATA WRITE IN OPERATING INSTRUCTION
304	ANALYSE THE START LOGICAL ADDRESS TO OBTAIN THE LOGICAL ADDRESS THAT SHOULD BE WROTE-IN
306	JUDGE THE PARITY OF SAID LOGICAL BLOCK ADDRESS
308	OPERATE ON THE PHYSICAL BLOCK WHICH CORRESPONDING TO SAID LOGICAL BLOCK ADDRESS AND IN THE FIRST FLASH CHIP
310	GO TO THE WRITING PROCESS ONE
312	OPERATE ON THE PHYSICAL BLOCK WHICH CORRESPONDING TO SAID LOGICAL BLOCK ADDRESS AND IN THE SECOND FLASH CHIP
314	GO TO THE WRITING PROCESS TWO
1	ODD
2	EVEN

(57) Abstract: The present invention provide a data write-in method of flash memory for writing data into two or more flash chips, the method comprise: priority corresponds the physical blocks in the two flash chips to the odd logical block address and the even logical block address respectively; analyse the logical block address which corresponds to the write-in operation from the data write-in instruction; judge the parity of said logical block address and select the corresponding flash chip according to the result; operate the flash chip, detect whether or not the other flash chip needs to be programmed or erased after direct the instruction to program or erase the flash chip, when the other flash chip needs to be programmed or erased, then direct the program or erase instruction to the other flash chip. Using the method of the present invention can program and erase two flash chips simultaneously, thereby increase the data write-in speed greatly.

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